



Name: AnM100HBA17M, AnM100LCA17M, AnM100RCA17M

Features:

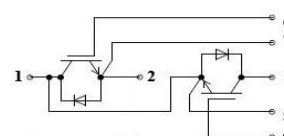
- Native Components
- Structure NPT+
- Low $V_{CE(sat)}$
- High short circuit capability
- Easy paralleling
- Positive temperature coefficient of $V_{CE(sat)}$
- Low C_{ies} , C_{oes} , C_{res}
- 100% control of the effect of double current
- Insulated base plate for heat dissipation
- Self-restraint on the short-circuit currents

Applications:

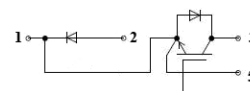
- AC inverter drives
- Switching (not for linear use)
- Public transport
- UPS



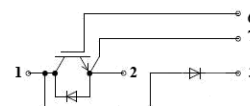
HB



RC



LC



Type	V_{CE}	I_C	Package	Packaging
AnM100HBA17M	1700 V	100 A	A – 34 mm	Box
AnM100LCA17M				
AnM100RCA17M				

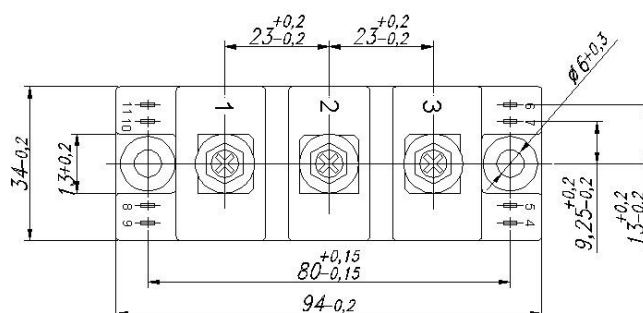
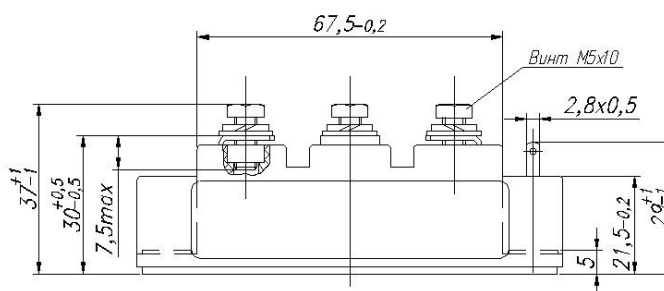




Table 1 – Absolute Maximum Rated Values

	Parameter		Units
IGBT			
V_{CES}	Collector-to-Emitter Voltage	1700	V
V_{GES}	Gate-to-Emitter Voltage	±20	V
$I_C, T_C=25\text{ }^{\circ}\text{C}$	Collector Current	140	A
$I_{CM}, T_C=25\text{ }^{\circ}\text{C}$	Pulsed Collector Current	280	
$I_C, T_C=80\text{ }^{\circ}\text{C}$	Collector Current	100	
$I_{CM}, T_C=80\text{ }^{\circ}\text{C}$	Pulsed Collector Current	200	
$P_D, T_C=25\text{ }^{\circ}\text{C}$	Maximum Dissipation	730	W
Inverse diode			
$I_F, T_C=25\text{ }^{\circ}\text{C}$	Forward Current	110	A
$I_{FM}, T_C=25\text{ }^{\circ}\text{C}$	Pulsed Forward Current	220	
$I_F, T_C=80\text{ }^{\circ}\text{C}$	Forward Current	80	
$I_{FM}, T_C=80\text{ }^{\circ}\text{C}$	Pulsed Emitter Current	160	
Free-Wheeling diode			
$I_F, T_C=25\text{ }^{\circ}\text{C}$	Forward Current	110	A
$I_{FM}, T_C=25\text{ }^{\circ}\text{C}$	Pulsed Forward Current	220	
$I_F, T_C=80\text{ }^{\circ}\text{C}$	Forward Current	80	
$I_{FM}, T_C=80\text{ }^{\circ}\text{C}$	Pulsed Emitter Current	160	
T_j	Operating Temperature	−55 to +150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	−55 to +125	
	Mounting Torque, M5	2.5 to 5.0	N * m
	Weight	200	g
V_{is}	Insulation Test Voltage ($t=1\text{ min.}$)	4000	Vrms

Table 2 – Thermal Resistance

Symbol	Parameter	Min	Max	Units	Test Conditions
R_{thJC}	Thermal Resistance, Junction-to-Case	–	0.17	$^{\circ}\text{C/W}$	Per IGBT
R_{thJCD}	Thermal Resistance, Junction-to-Case	–	0.32		Per FWD

Table 3 – Electrical Characteristics @ $T_J=25\text{ }^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IGBT						
$V_{CE(sat)}$	Collector-to-Emitter Saturation Voltage	–	2.2	3.0	V	$V_{GE}=15\text{ V}$, $I_C=100\text{ A}^{(3)}$
		–	2.4	3.5		$V_{GE}=15\text{ V}$, $I_C=100\text{ A}^{(3)}$, $T_J=125\text{ }^{\circ}\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	6.0	7.0	V	$V_{GE}=V_{GES}$, $I_C=5.0\text{ mA}$
I_{CES}	Zero Gate Voltage Collector Current	–	0.02	0.5	mA	$V_{CE}=1700\text{ V}$, $V_{GE}=0\text{ V}$
		–	0.9	5.0		$V_{CE}=1700\text{ V}$, $V_{GE}=0\text{ V}$, $T_J=125\text{ }^{\circ}\text{C}$
$I_{GES(F)}$	Gate-to-Source Leakage Forward	–	10	100	nA	$V_{GE}=20\text{ V}$
		–	20	150		$V_{GE}=20\text{ V}$, $T_J=125\text{ }^{\circ}\text{C}$
$I_{GES(R)}$	Gate-to-Source Leakage Reverse	–100	–10	–		$V_{GE}=-20\text{ V}$
		–150	–20	–		$V_{GE}=-20\text{ V}$, $T_J=125\text{ }^{\circ}\text{C}$
C_{ies}	Input Capacitance	–	8.9	–	nF	$V_{GE}=0\text{ V}$, $V_{CE}=25\text{ V}$, $f=1\text{ MHz}$
C_{oes}	Output Capacitance	–	0.9	–		
C_{res}	Reverse Transfer Capacitance	–	0.4	–		
$t_{d(on)}$	Turn-On Delay Time	–	100	–	ns	$V_{CC}=850\text{ V}$, $I_C=100\text{ A}$, $V_{GE}=15\text{ V}$, $R_G=10\text{ }\Omega$, $T_J=125\text{ }^{\circ}\text{C}$, Inductive Load
t_r	Rise Time	–	150	–		
$t_{d(off)}$	Turn-Off Delay Time	–	450	–		
t_f	Fall Time	–	130	–		
E_{on}	Turn-On Energy	–	15	–	mJ	$V_{CC}=850\text{ V}$, $I_C=100\text{ A}$, $V_{GE}=15\text{ V}$, $R_G=10\text{ }\Omega$, $T_J=125\text{ }^{\circ}\text{C}$, Inductive Load
E_{off}	Turn-Off Energy	–	11	–		
E_{tot}	Total Energy	–	26	–		
I_{sc}	Short circuit collector current	–	400	–	A	$t_p \leq 10\text{ }\mu\text{sec}$, $V_{GE} \leq 15\text{ V}$, $R_G=10\text{ }\Omega$, $T_J=125\text{ }^{\circ}\text{C}$, $V_{CC}=1000\text{ V}$, $V_{CEmax}=V_{CES}-L_{sCE} \cdot di/dt$

**Inverse and Free-Wheeling Diode**

V_F	Forward Voltage	–	1.9	2.5	V	$I_F=100\text{ A}$, $V_{GE}=0\text{ V}$
I_{rrm}	Maximum Reverse Recovery Current	–	60	–	A	$I_F=100\text{ A}$, $di_F/dt=0.5\text{ A/ns}$, $V_{GE}=0\text{ V}$, $T_j=25\text{ °C}$
t_{rr}	Diode Reverse Recovery Time	–	180	300	ns	
Q_{rr}	Diode Reverse Recovery Charge	–	10	–	μC	

Precious metal content into 1000 pieces:

Gold _____ g;

Silver _____g.

***Table 4 – Revision history***

Date	Revision	Changes
03-October-2014	1	Complete version. Preliminary.
30-Sep-2016	2	Correct contacts. Add topology left and right chopper.